

# UP03396

Silicon NPN epitaxial planar type (Tr1)  
Silicon PNP epitaxial planar type (Tr2)

For digital circuits

## ■ Features

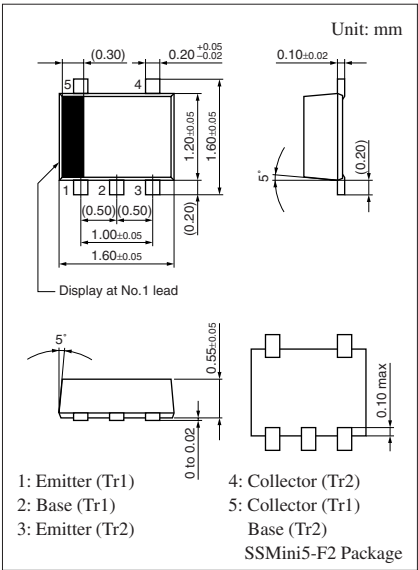
- Two elements incorporated into one package  
(Transistors with built-in resistor)
- Reduction of the mounting area and assembly cost by one half

## ■ Basic Part Number

- UNR111T + UNR1211

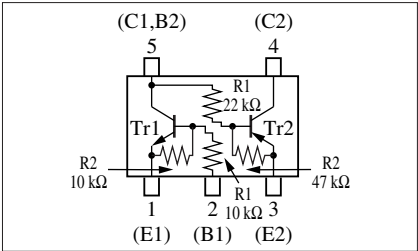
## ■ Absolute Maximum Ratings $T_a = 25^{\circ}\text{C}$

| Parameter |  | Symbol    | Rating      | Unit               |
|-----------|--|-----------|-------------|--------------------|
| Tr1       | Collector-base voltage<br>(Emitter open) | $V_{CBO}$ | 50          | V                  |
|           | Collector-emitter voltage<br>(Base open) | $V_{CEO}$ | 50          | V                  |
|           | Collector current                        | $I_C$     | 100         | mA                 |
| Tr2       | Collector-base voltage<br>(Emitter open) | $V_{CBO}$ | -50         | V                  |
|           | Collector-emitter voltage<br>(Base open) | $V_{CEO}$ | -50         | V                  |
|           | Collector current                        | $I_C$     | -100        | mA                 |
| Overall   | Total power dissipation                  | $P_T$     | 125         | mW                 |
|           | Junction temperature                     | $T_j$     | 125         | $^{\circ}\text{C}$ |
|           | Storage temperature                      | $T_{stg}$ | -55 to +125 | $^{\circ}\text{C}$ |



Marking Symbol: 6P

Internal Connection



# ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

## • Tr1

| Parameter                                    | Symbol                        | Conditions  | Min  | Typ | Max  | Unit             |
|--|-------------------------------|---|------|-----|------|------------------|
| Collector-base voltage (Emitter open)        | $V_{\text{CBO}}$              | $I_{\text{C}} = 10\ \mu\text{A}$ , $I_{\text{E}} = 0$   | 50   |     |      | V                |
| Collector-emitter voltage (Base open)        | $V_{\text{CEO}}$              | $I_{\text{C}} = 2\ \text{mA}$ , $I_{\text{B}} = 0$  | 50   |     |      | V                |
| Collector-base cutoff current (Emitter open) | $I_{\text{CBO}}$              | $V_{\text{CB}} = 50\ \text{V}$ , $I_{\text{E}} = 0$   |      |     | 0.1  | $\mu\text{A}$    |
| Collector-emitter cutoff current (Base open) | $I_{\text{CEO}}$              | $V_{\text{CE}} = 50\ \text{V}$ , $I_{\text{B}} = 0$   |      |     | 0.5  | $\mu\text{A}$    |
| Emitter-base cutoff current (Collector open) | $I_{\text{EBO}}$              | $V_{\text{EB}} = 6\ \text{V}$ , $I_{\text{C}} = 0$  |      |     | 0.5  | mA               |
| Forward current transfer ratio               | $h_{\text{FE}}$               | $V_{\text{CE}} = 10\ \text{V}$ , $I_{\text{C}} = 5\ \text{mA}$                                      | 35   |     |      | —                |
| Collector-emitter saturation voltage         | $V_{\text{CE(sat)}}$          | $I_{\text{C}} = 10\ \text{mA}$ , $I_{\text{B}} = 0.3\ \text{mA}$                                    |      |     | 0.25 | V                |
| Output voltage high-level                    | $V_{\text{OH}}$               | $V_{\text{CC}} = 5\ \text{V}$ , $V_{\text{B}} = 0.5\ \text{V}$ , $R_{\text{L}} = 1\ \text{k}\Omega$ | 4.9  |     |      | V                |
| Output voltage low-level                     | $V_{\text{OL}}$               | $V_{\text{CC}} = 5\ \text{V}$ , $V_{\text{B}} = 2.5\ \text{V}$ , $R_{\text{L}} = 1\ \text{k}\Omega$ |      |     | 0.2  | V                |
| Input resistance                             | $R_{\text{I}}$                |   | -30% | 10  | +30% | $\text{k}\Omega$ |
| Resistance ratio                             | $R_{\text{I}} / R_{\text{2}}$ |   | 0.8  | 1.0 | 1.2  | —                |
| Transition frequency                         | $f_{\text{T}}$                | $V_{\text{CB}} = 10\ \text{V}$ , $I_{\text{E}} = -2\ \text{mA}$ , $f = 200\ \text{MHz}$             |      | 150 |      | MHz              |

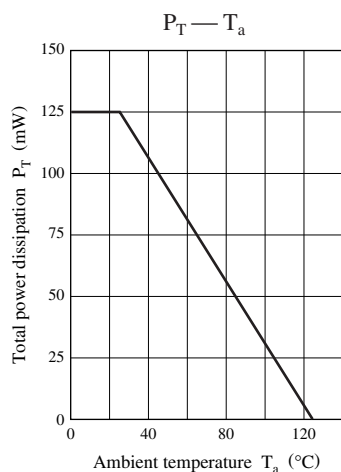
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

## • Tr2

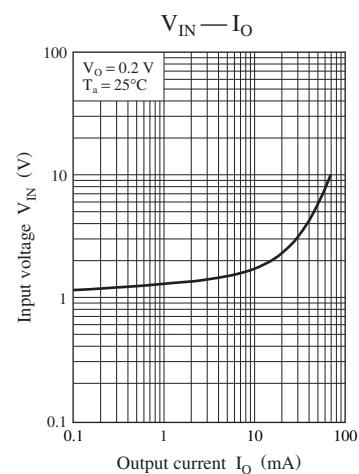
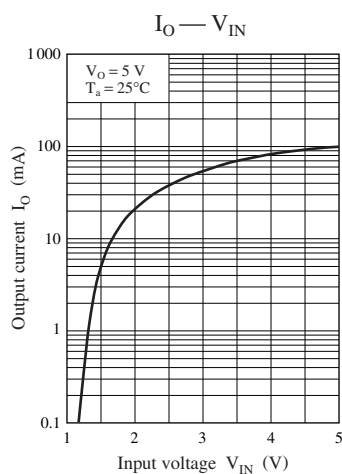
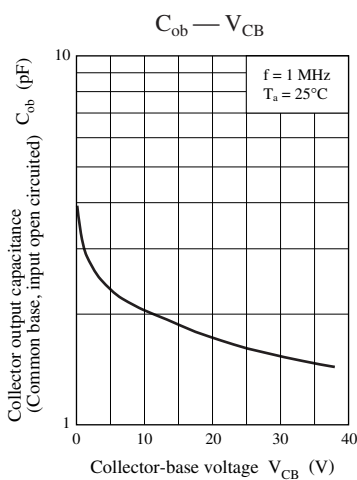
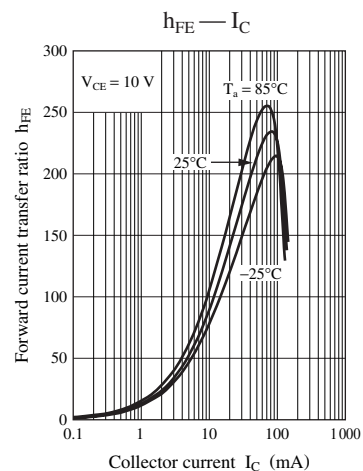
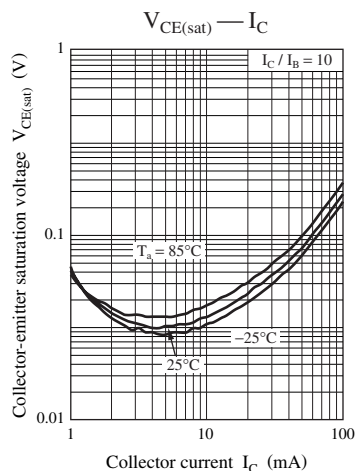
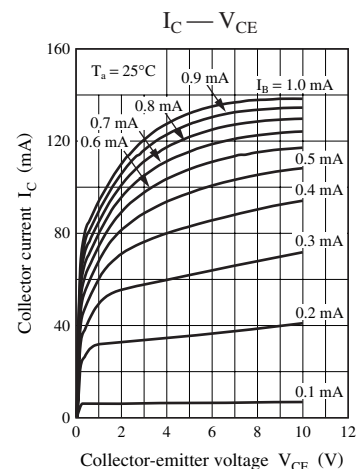
| Parameter                                    | Symbol                        | Conditions  | Min  | Typ  | Max   | Unit             |
|--|-------------------------------|---|------|------|-------|------------------|
| Collector-base voltage (Emitter open)        | $V_{\text{CBO}}$              | $I_{\text{C}} = -10\ \mu\text{A}$ , $I_{\text{E}} = 0$  | -50  |      |       | V                |
| Collector-emitter voltage (Base open)        | $V_{\text{CEO}}$              | $I_{\text{C}} = -2\ \text{mA}$ , $I_{\text{B}} = 0$   | -50  |      |       | V                |
| Collector-base cutoff current (Emitter open) | $I_{\text{CBO}}$              | $V_{\text{CB}} = -50\ \text{V}$ , $I_{\text{E}} = 0$  |      |      | -0.1  | $\mu\text{A}$    |
| Collector-emitter cutoff current (Base open) | $I_{\text{CEO}}$              | $V_{\text{CE}} = -50\ \text{V}$ , $I_{\text{B}} = 0$  |      |      | -0.5  | $\mu\text{A}$    |
| Emitter-base cutoff current (Collector open) | $I_{\text{EBO}}$              | $V_{\text{EB}} = -6\ \text{V}$ , $I_{\text{C}} = 0$   |      |      | -0.2  | mA               |
| Forward current transfer ratio               | $h_{\text{FE}}$               | $V_{\text{CE}} = -10\ \text{V}$ , $I_{\text{C}} = -5\ \text{mA}$                                      | 80   |      | 400   | —                |
| Collector-emitter saturation voltage         | $V_{\text{CE(sat)}}$          | $I_{\text{C}} = -10\ \text{mA}$ , $I_{\text{B}} = -0.3\ \text{mA}$                                    |      |      | -0.25 | V                |
| Output voltage high-level                    | $V_{\text{OH}}$               | $V_{\text{CC}} = -5\ \text{V}$ , $V_{\text{B}} = -0.5\ \text{V}$ , $R_{\text{L}} = 1\ \text{k}\Omega$ | -4.9 |      |       | V                |
| Output voltage low-level                     | $V_{\text{OL}}$               | $V_{\text{CC}} = -5\ \text{V}$ , $V_{\text{B}} = -2.5\ \text{V}$ , $R_{\text{L}} = 1\ \text{k}\Omega$ |      |      | -0.2  | V                |
| Input resistance                             | $R_{\text{I}}$                |   | -30% | 22   | +30%  | $\text{k}\Omega$ |
| Resistance ratio                             | $R_{\text{I}} / R_{\text{2}}$ |   |      | 0.47 |       | —                |
| Transition frequency                         | $f_{\text{T}}$                | $V_{\text{CB}} = -10\ \text{V}$ , $I_{\text{E}} = 1\ \text{mA}$ , $f = 200\ \text{MHz}$               |      | 80   |       | MHz              |

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

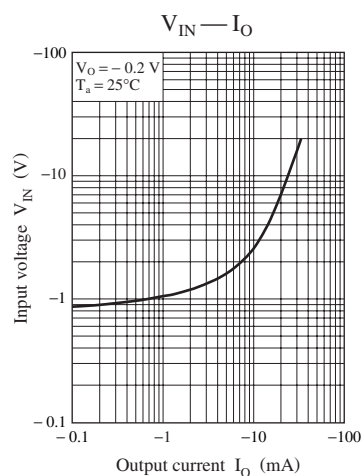
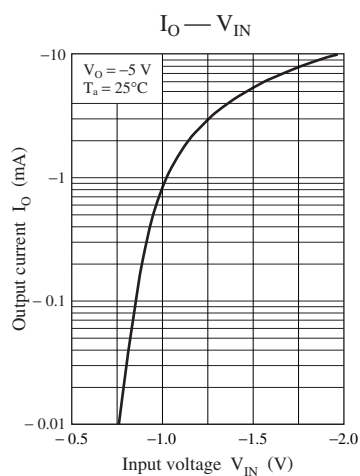
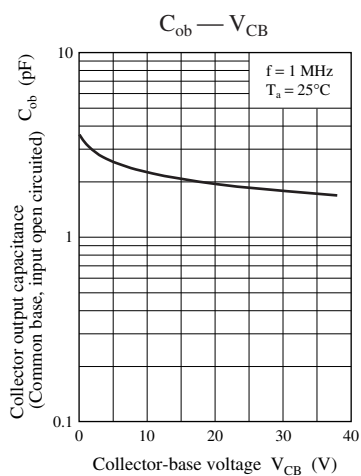
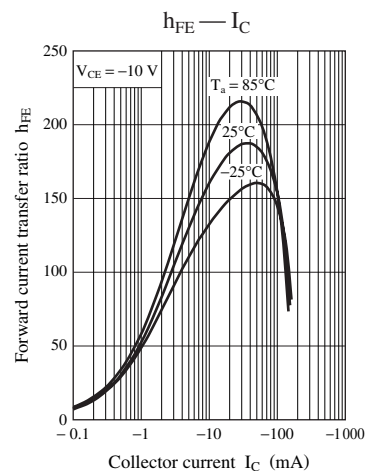
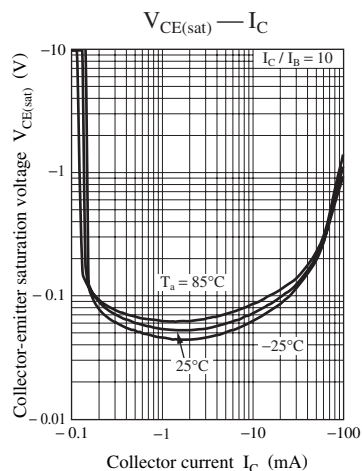
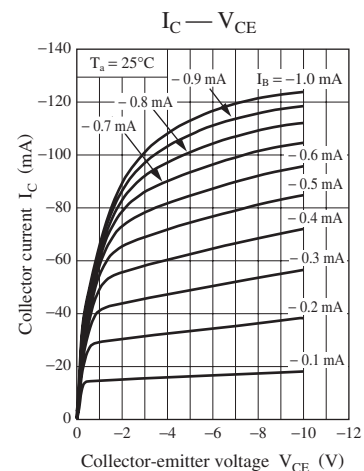
## Common characteristics chart



## Characteristics charts of Tr1



## Characteristics charts of Tr2



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